

Silicon Carbide Wafer N TYPE

Product Description

SiC wafer is a next generation semiconductor material, with unique electrical properties and excellent thermal properties, compared to silicon wafer and GaAs wafer, SiC wafer is more suitable for high temperature and high power device application. Silicon Carbide based devices have been used for short wavelength opto-electronic, high temperature, radiation resistant applications.

- Totally customized
- Low and medium volumes
- Any diameter
- Any orientations
- Any thickness

Typical Properties

Dopant	:	Nitrogen
Type	:	N
Resistivity	:	0.012-0.0028Ω.Cm
Secondary flat length	:	(8 ± 1.7) mm
Primary flat length	:	(16 ± 1.7) mm
Primary flat orientation	:	Parallel {1-100} ± 5°
FWHM	:	A < 30 arcsec
Surface Finish	:	Single or double face polished

Applications

- ✓ R&D and manufacturing
- ✓ Resistive touch panel application
- ✓ Automobiles, aerospace and drone technology
- ✓ AI (Artificial Intelligence)
- ✓ MEMS fabrication
- ✓ Transistors, diodes, and rectifiers
- ✓ Robotics
- ✓ Solar cell
- ✓ MEMS, Biotechnology
- ✓ Optical sensors

Key Features

Product	:	Silicon Carbide Wafer N Types
Stock No	:	NS6130-10-1156
Diameter	:	2"
Thickness	:	430±25μm



NS6130-10-1156

2"
Inch
N Type

Follow us:

    | www.nanoshel.com | sales@nanoshel.com

